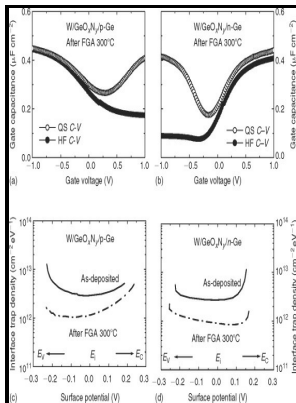


Preparation and the physical properties of CdSe-Ge heterojunctions.

University of Salford - Blue emission at atomically sharp 1D heterojunctions between graphene and h



Description: -

-Preparation and the physical properties of CdSe-Ge heterojunctions.

-Preparation and the physical properties of CdSe-Ge heterojunctions.

Notes: PhD thesis, Electrical Engineering.

This edition was published in 1969



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Tags: #604. #Some #electrical #and #photoelectric #properties #of #p-Si-CdSe #heterojunctions: #B #N #Zvonkov #and #I #A #Karpovich, #Izv #VUZ #Fiz, #No #10, #1970, #116

Two

USSR The possibility of crystallizing vitreous selenium and chalcogenide glasses As₂Se₃. It is obvious that only conventional magnetoresistance without rectification effect can not induce any rectification MR either, as shown in. To remove the excess thermal effect, all the gain mediums were wrapped by indium foil and mounted in a copper block with water cooled at 16°C.

Facile one

Under the absorbed pump power of 6. His recent research focuses on macrostructural assembly and engineering of nanomaterials e.

Large rectification magnetoresistance in nonmagnetic Al/Ge/Al heterojunctions

The findings of rectification magnetoresistance open the way to the new nonmagnetic Ge-based spintronics devices of large rectification magnetoresistance at ambient temperature under the alternating-current due to the simultaneous implementation of the rectification and magnetoresistance in the same devices.

Two

The atomic ratio of Te and P is approximately 1:1, indicating the purity of the sample. USSR The properties of p-Si-CdSe heterojunctions are investigated.

Enhanced ammonia sensing properties of rGO/WS2 heterojunction based chemiresistive sensor by marginal sulfonate decoration

Anisotropic magnetoresistance in ferromagnetic 3d alloys. It is speculated that the bonding with the substrate can counteract the effect of the

dangling bonds and stabilize the formation of low-buckling stanene.

Large rectification magnetoresistance in nonmagnetic Al/Ge/Al heterojunctions

With a suitable ultrasonic power, small MoS₂ nanosheets with dozens of nanometer diameter can be obtained to adhere to graphene layers with tens of micrometer-scale diameter. Enhanced low field magnetoresistance in germanium and silicon-diode combined devices at room temperature.

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